



Internet Assistant (defaultmine.wspst)

Drafts  
Pending  
Active  
L1: (33) (selective) with(laser) with (nitride)  
L2: (2781495) @ad<19990104  
L3: (16) 1 and 2  
L4: (17) 1 not 3  
L5: (1) (\*6214684\*).PN.  
L6: (189353) mask or masks  
L7: (15) 4 and 6  
L8: (68) (selective or selectively) with(laser) with (nitride)  
L9: (35) 2 and 8  
L10: (69) (selective or selectively) with(laser) with (nitride or nitriding)  
Failed  
Saved  
Favorites  
Tagged (0)  
UDC  
Queue  
Trash

USPAT,USPGPUB  
Default operator: ON  
Highlight all the terms initially

3 and 10

	U	I	Document	Issue Da	Page	Title	Current	Current X	Retrieval	Inventor	S	C	P	2	3
1	F	F	US 200200	2002042	9	GALLIUMNITRIDE	372/46	372/45		KIMURA, AKITA	F	F	F	F	F
2	F	F	US 657759	2002042	59	Semiconductor materials, m	372/45	257/52,		Tanaka, Toshiaki, et	F	F	F	F	F

Ready



FAST - [detail.htm: wsp:1]

File View Edit Tools Window Help

Drafts  
Pending  
Active  
L1: (1702) nitridation  
L2: (1S639S) laser  
L3: (1S4619) nm or nanometer or nanometers  
L4: (317960) silicon or Si  
L5: (1S4016) polysilicon or "poly-Si" or "poly Si" or "polycrystalline silicon" or "polycryst..."  
L6: (250S44) selective  
L7: (34) 1 and 2 and 3 and 4 and 5 and 6  
L8: (1) 1 with 2 with 6  
L9: (14) 1 with 2  
L10: (7) 8 and 9  
Failed  
Saved  
Favorites  
Tagged (0)  
UDC  
Queue  
Trash

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6207514 B1	20010327	17	Method for forming borderless gate structures and apparatus formed t	43S/299	43S/293
2	<input type="checkbox"/>	<input type="checkbox"/>	US 5977612 A	19991102	20	Semiconductor devices constructed	257/61S	257/103

Ready

EAST - [default.wsp:1]

File View Edit Tools Window Help

Drafts  
Pending  
Active  
L1: (13) laser with nitridation  
L2: (13910) "laser assisted" or nitridize or nitridizes or nitridizing or nitridization or nitrid...  
L3: (13915) 1 or 2  
L4: (1980711) trimm\$ or reduce\$ or remove\$  
L5: (34884) 4 with gate  
L6: (729) 3 and 5  
L7: (671) ("438/585") or ("438/705") or ("438/775"): CCLS.  
L8: (0) ("6 and 7"):PN.  
L9: (38) 6 and 7  
Failed  
Saved  
Favorites  
Tagged  
UDC  
Queue  
Trash

6 and 7

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6235590 B1	20010522	9	Fabrication of differential gate oxide thicknesses on a single integrated	438/275	438/769 438/775

Ready



EAST - [default.wsp:1]

File View Edit Tools Window Help

Active

- L1: (671) (('438/585") or ('438/705") or ('438/775")).CCLS.
- L2: (48527) trimm\$
- L3: (438) 2 with gate
- L4: (4) 1 and 3
- L5: (1) "5330936".PN.
- L6: (1) "5358879".PN.
- L7: (1) "5545581".PN.
- L8: (1972617) reduce\$ or remove\$
- L9: (1980711) 2 or 8
- L10: (34884) 9 with gate
- L11: (274) 1 and 10
- L12: (165872) poly or polysilicon or "polycrystalline silicon" or "poly-Si" or "poly silicon"
- L13: (248) 11 and 12
- L14: (1) ("6204130").PN.
- L15: (947908) N or nitridation or nitrogen
- L16: (1) 14 and 15
- L17: (17) 15 and 11

Failed

Saved

U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef

Ready

above. For instance, various features of the above embodiments can be combined with others. An additional polish-stop layer can be formed on the top surface of the substrate before the etching the trench. Alternatively, if desired, the gate electrode material can be polished until it is aligned with the top surface of the substrate. The channel implant may not be essential and can provide enhancement-mode doping if desired. The source and drain can be spaced from the sidewalls, as long as they are adjacent to the bottom surface of the trench. Likewise, the insulative spacers need not necessarily extend to the top surface of the substrate, as long as the gate electrode remains electrically isolated from the substrate. The gate electrode can be patterned to extend beyond the trench length over the substrate. The gate electrode can be other conductors such as aluminum, titanium, tungsten, cobalt, and combinations thereof, although the material may be limited by the use of subsequent high-temperature steps. The gate insulator and insulative spacers can be various dielectrics including oxides, nitrides, and oxynitrides, formed in various manners that include deposition, tube growth and rapid thermal anneal growth. The insulative spacers can also be undoped polysilicon formed on the sidewall insulators and gate insulator. A polysilicon gate electrode can be deposited doped or undoped, and if deposited undoped can be doped either before or after it is polished. The N-type and P-type dopants can be reversed. Suitable P-type dopants include boron B.sub.10, boron B.sub.11, and BF.sub.x species such as BF.sub.2.

L Number	Hits	Search Text	DB	Time stamp
1	33	(selective) with(laser) with (nitride)	USPAT; US-PGPUB	2003/06/23 16:59
2	2781495	@ad<19990104	USPAT; US-PGPUB	2003/06/23 16:36
3	16	((selective) with(laser) with (nitride)) and @ad<19990104	USPAT; US-PGPUB	2003/06/23 16:39
4	17	((selective) with(laser) with (nitride)) not (((selective) with(laser) with (nitride)) and @ad<19990104)	USPAT; US-PGPUB	2003/06/23 16:42
5	1	("6214684").PN.	USPAT; US-PGPUB	2003/06/23 16:50
6	189353	mask or masks	USPAT; US-PGPUB	2003/06/23 16:51
7	15	((selective) with(laser) with (nitride)) not (((selective) with(laser) with (nitride)) and @ad<19990104)) and (mask or masks)	USPAT; US-PGPUB	2003/06/23 16:51
8	68	(selective or selectively) with(laser) with (nitride)	USPAT; US-PGPUB	2003/06/23 16:56
9	35	@ad<19990104 and ((selective or selectively) with(laser) with (nitride))	USPAT; US-PGPUB	2003/06/23 16:57
10	69	(selective or selectively) with(laser) with (nitride or nitriding)	USPAT; US-PGPUB	2003/06/23 16:59
11	36	@ad<19990104 and ((selective or selectively) with(laser) with (nitride or nitriding))	USPAT; US-PGPUB	2003/06/23 16:59